

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of	:	
	:	Group Art Unit: Unknown
Remmel, et al.	:	
	:	
Serial No.: Not yet assigned	:	Examiner: Unknown
	:	
Filed: Herewith	:	
	:	
Title: Method of Making A Semiconductor Device, and Semiconductor Device Made Thereby	:	

INFORMATION DISCLOSURE STATEMENT

Mail Stop Patent Application
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir: :

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authorized to charge any fee deficiency required by this paper or credit any overpayment to
Deposit Account No. 02-4467.

Respectfully submitted,

Dated: March 10, 2004

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Thomas LeVance
Printed Name: Thomas LeVance

FORM PTO- 1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. 0139376	SERIAL NO
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)		APPLICANT Remmel, et al.	
		FILING DATE March 10, 2004	GROUP

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,500,724	12/31/02	Zurcher et al.			
	6,180,976	1/30/01	Roy			
	5,926,359	7/20/99	Greco et al.			
	5,731,747	3/24/98	Van De Walle, et al.			
	5,708,559	1/13/98	Brabazon, et al.			
	6,117,747	9/12/00	Shao, et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
	2000228497	8/15/00	Japan			No	

OTHER DOCUMENTS (Including Author, Title, Date Pertinent Pages, Etc.)

	Yoshitomi et al., <u>High Performance MIM Capacitor for RF BiCMOS/CMOS LSIs; Proc. of the BCTM</u> , pp. 133-36, 1999.
	Lui et al., <u>Single Mask Metal-Insulator-Metal (MIM) Capacitor with Copper Damascene Metallization for Sub-0.18μm Mixed Mode Signal and System-on-a-Chip (SoC) Applications; IEEE</u> , pp. 111-13, 2000.
	Mahnkopf et al., <u>'System on a Chip' Technology Platform for 0.18μm Digital, Mixed Signal & eDRAM Applications, IEDM</u> , pp. 849-52, 1999.
	Bolam et al., <u>Electrical Characteristics and Reliability of UV Transparent Si₃N₄ Metal-Insulator-Metal (MIM) Capacitors, IEEE Transactions on Electron Devices</u> , Vol. 50, No. 4, pp. 941-44, 2003.

EXAMINER

DATE
CONSIDERED

EXAMINER: Initial citation considered. Draw line through citation if not in the conformance and not considered. Include copy of this form with next communication to applicant.

(Form PTO-1449)